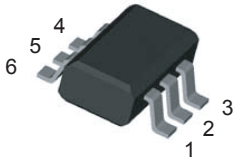
CEH2331

P-Channel Enhancement Mode Field Effect Transistor

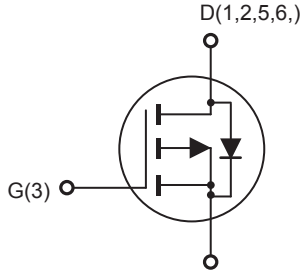
PRELIMINARY

FEATURES

- -20V, -5.2A , $R_{DS(ON)}$ = 48mΩ @V_{GS} = -4.5V.
  $R_{DS(ON)}$ = 60mΩ @V_{GS} = -2.5V.
  $R_{DS(ON)}$ = 78mΩ @V_{GS} = -1.8V.
- High dense cell design for extremely low $R_{DS(ON)}$.
- Rugged and reliable.
- Lead free product is acquired.
- TSOP-6 package.



TSOP-6



ABSOLUTE MAXIMUM RATINGS T_A = 25°C unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-5.2	A
Drain Current-Pulsed [a]	I_{DM}	-21	A
Maximum Power Dissipation	P_D	2.0	W
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient [b]	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics T_A = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = -250μA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -20V, V_{GS} = 0V			1	μA
Gate Body Leakage Current	I_{GSS}	V_{GS} = ±12V, V_{DS} = 0V			±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	-0.4		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -3.3A		36	48	mΩ
		V_{GS} = -2.5V, I_D = -2.8A		46	60	mΩ
		V_{GS} = -1.8V, I_D = -2A		60	78	mΩ
Dynamic Characteristics [d]						
Forward Transconductance	g_{FS}	V_{DS} = -5V, I_D = -4A		13		S
Input Capacitance	C_{iss}	V_{DS} = -10V, V_{GS} = 0V, f = 1.0 MHz		965		pF
Output Capacitance	C_{oss}			200		pF
Reverse Transfer Capacitance	C_{rss}			155		pF
Switching Characteristics [d]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10V, I_D = -4A, V_{GS} = -4.5V, R_{GEN} = 3Ω		15	30	ns
Turn-On Rise Time	t_r			10	20	ns
Turn-Off Delay Time	$t_{d(off)}$			40	80	ns
Turn-Off Fall Time	t_f			13	26	ns
Total Gate Charge	Q_g	V_{DS} = -10V, I_D = -4A, V_{GS} = -4.5V		13	17	nC
Gate-Source Charge	Q_{gs}			2.5		nC
Gate-Drain Charge	Q_{gd}			3		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current [b]	I_S				-5.2	A
Drain-Source Diode Forward Voltage [c]	V_{SD}	V_{GS} = 0V, I_S = -1A			-1.2	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature.
b.Surface Mounted on FR4 Board, t ≤ 5 sec.
c.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
d.Guaranteed by design, not subject to production testing.

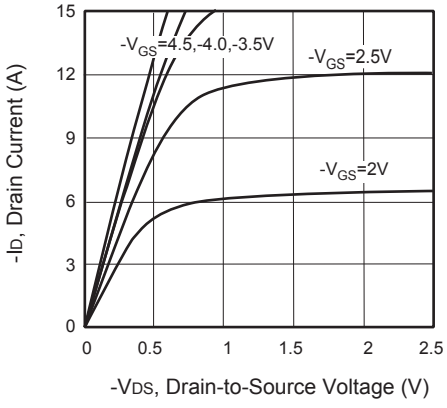


Figure 1. Output Characteristics

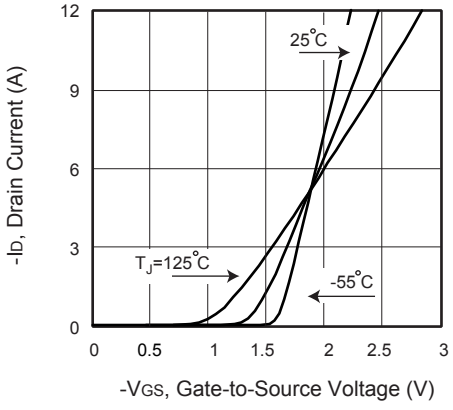


Figure 2. Transfer Characteristics

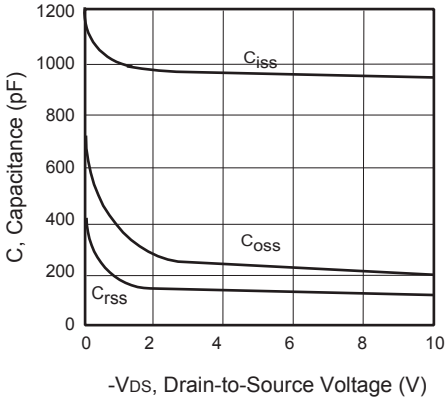


Figure 3. Capacitance

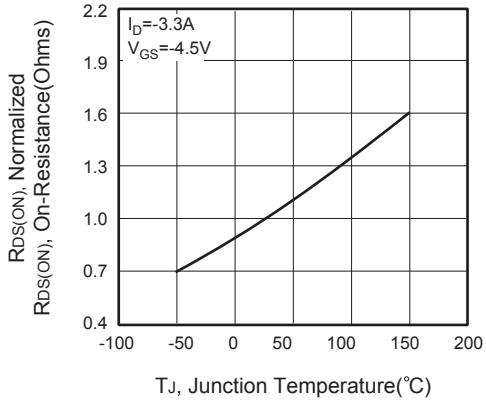


Figure 4. On-Resistance Variation with Temperature

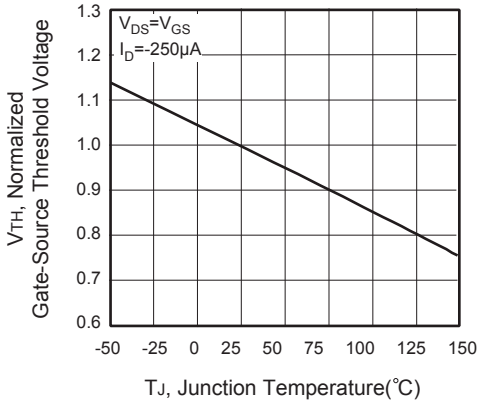


Figure 5. Gate Threshold Variation with Temperature

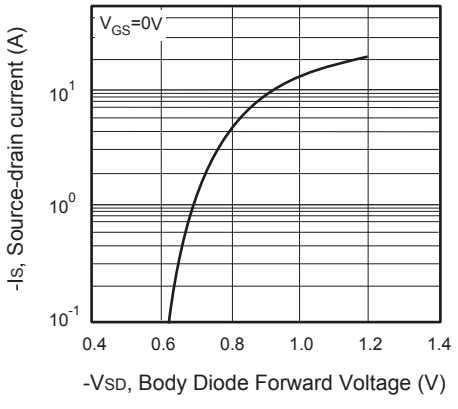


Figure 6. Body Diode Forward Voltage Variation with Source Current

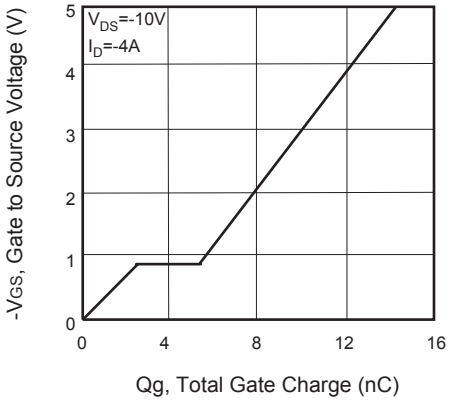


Figure 7. Gate Charge

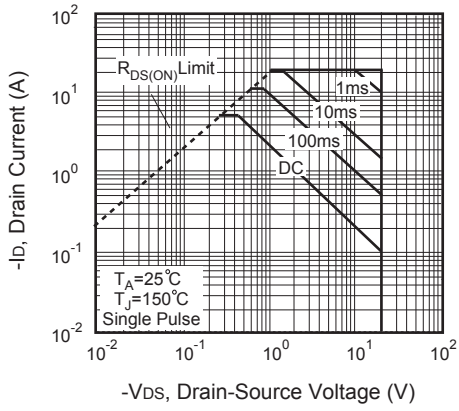


Figure 8. Maximum Safe Operating Area

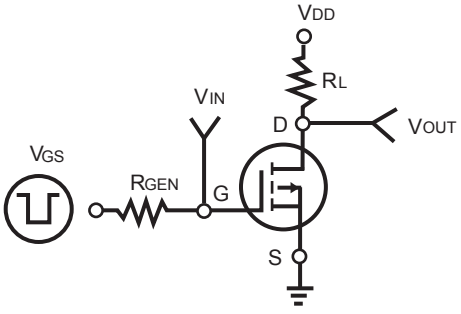


Figure 9. Switching Test Circuit

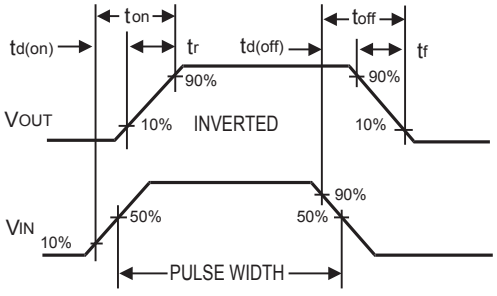


Figure 10. Switching Waveforms